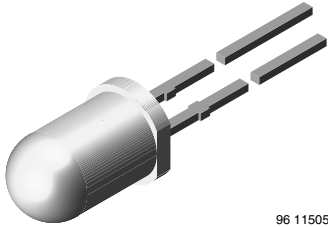


High Power Infrared Emitting Diode, Vishay Semiconductors 940 nm, GaAlAs/GaAs



96 11505

DESCRIPTION

TSAL5300 is an infrared, 940 nm emitting diode in GaAlAs/GaAs technology with high radiant power molded in a blue-gray plastic package.

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): \varnothing 5
- Leads with stand-off
- Peak wavelength: $\lambda_p = 940$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\varphi = \pm 22^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Infrared remote control units with high power requirements
- Free air transmission systems
- Infrared source for optical counters and card readers

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSAL5300	45	± 22	940	800

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSAL5300	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSAL5300-MSZ	Tape and ammpack	MOQ: 5000 pcs, 1000 pcs/ammpack	T-1 $\frac{3}{4}$

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I_{FM}	200	mA
Surge forward current	$t_p = 100 \mu s$	I_{FSM}	1.5	A
Power dissipation		P_V	160	mW
Junction temperature		T_j	100	$^\circ C$
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ C$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ C$
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ C$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R_{thJA}	230	K/W

Note

$T_{amb} = 25$ $^\circ C$, unless otherwise specified

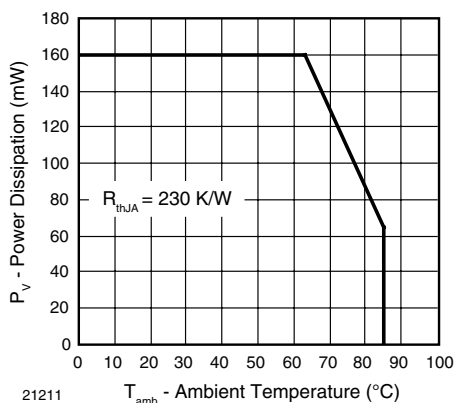


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

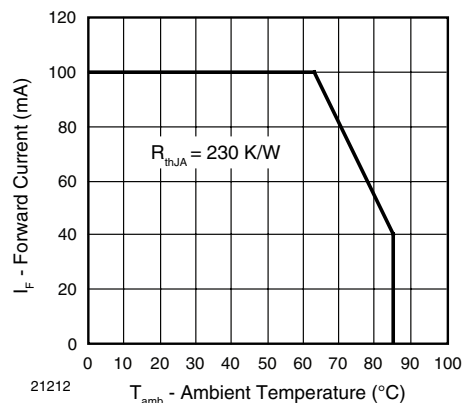


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V_F		1.35	1.6	V
	$I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$	V_F		2.6	3	V
Temperature coefficient of V_F	$I_F = 1 \text{ mA}$	TK_{V_F}		- 1.8		mV/K
Reverse current	$V_R = 5 \text{ V}$	I_R			10	μA
Junction capacitance	$V_R = 0 \text{ V}, f = 1 \text{ MHz}, E = 0$	C_j		25		pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	I_e	30	45	150	mW/sr
	$I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$	I_e	260	350		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	ϕ_e		35		mW
Temperature coefficient of ϕ_e	$I_F = 20 \text{ mA}$	TK_{ϕ_e}		- 0.6		%/K
Angle of half intensity		φ		± 22		deg
Peak wavelength	$I_F = 100 \text{ mA}$	λ_p		940		nm
Spectral bandwidth	$I_F = 100 \text{ mA}$	$\Delta\lambda$		50		nm
Temperature coefficient of λ_p	$I_F = 100 \text{ mA}$	TK_{λ_p}		0.2		nm/K
Rise time	$I_F = 100 \text{ mA}$	t_r		800		ns
	$I_F = 1 \text{ A}$	t_r		500		ns
Fall time	$I_F = 100 \text{ mA}$	t_f		800		ns
	$I_F = 1 \text{ A}$	t_f		500		ns
Virtual source diameter	Method: 63 % encircled energy	d		2.3		mm

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

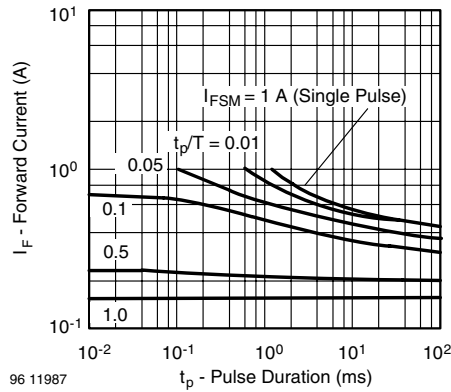
BASIC CHARACTERISTICS
 $T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified


Fig. 3 - Pulse Forward Current vs. Pulse Duration

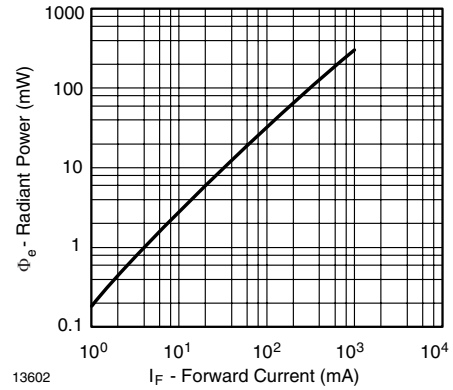


Fig. 6 - Radiant Power vs. Forward Current

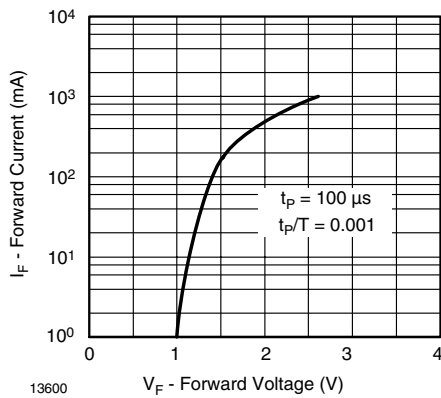


Fig. 4 - Forward Current vs. Forward Voltage

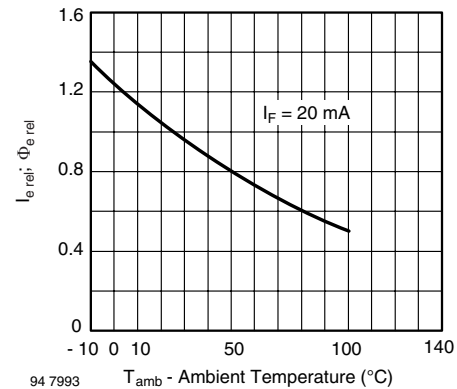


Fig. 7 - Relative Radiant Intensity/Power vs. Ambient Temperature

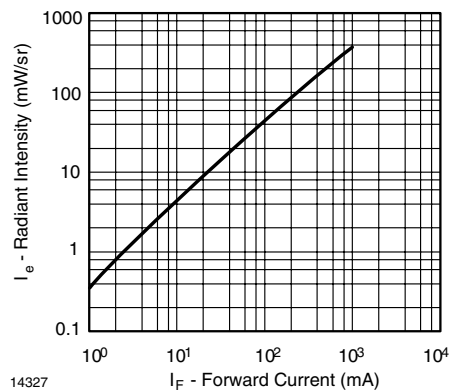


Fig. 5 - Radiant Intensity vs. Forward Current

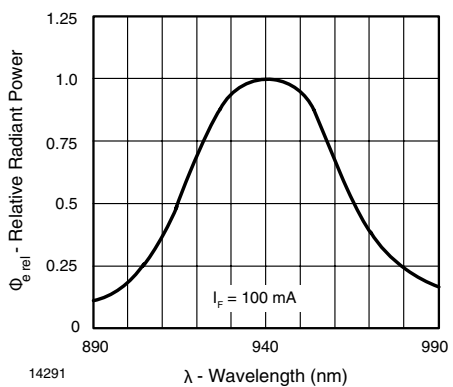


Fig. 8 - Relative Radiant Power vs. Wavelength

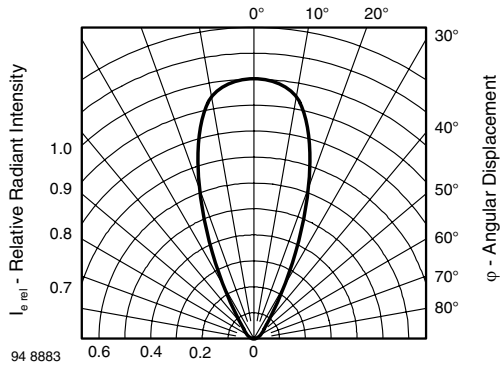
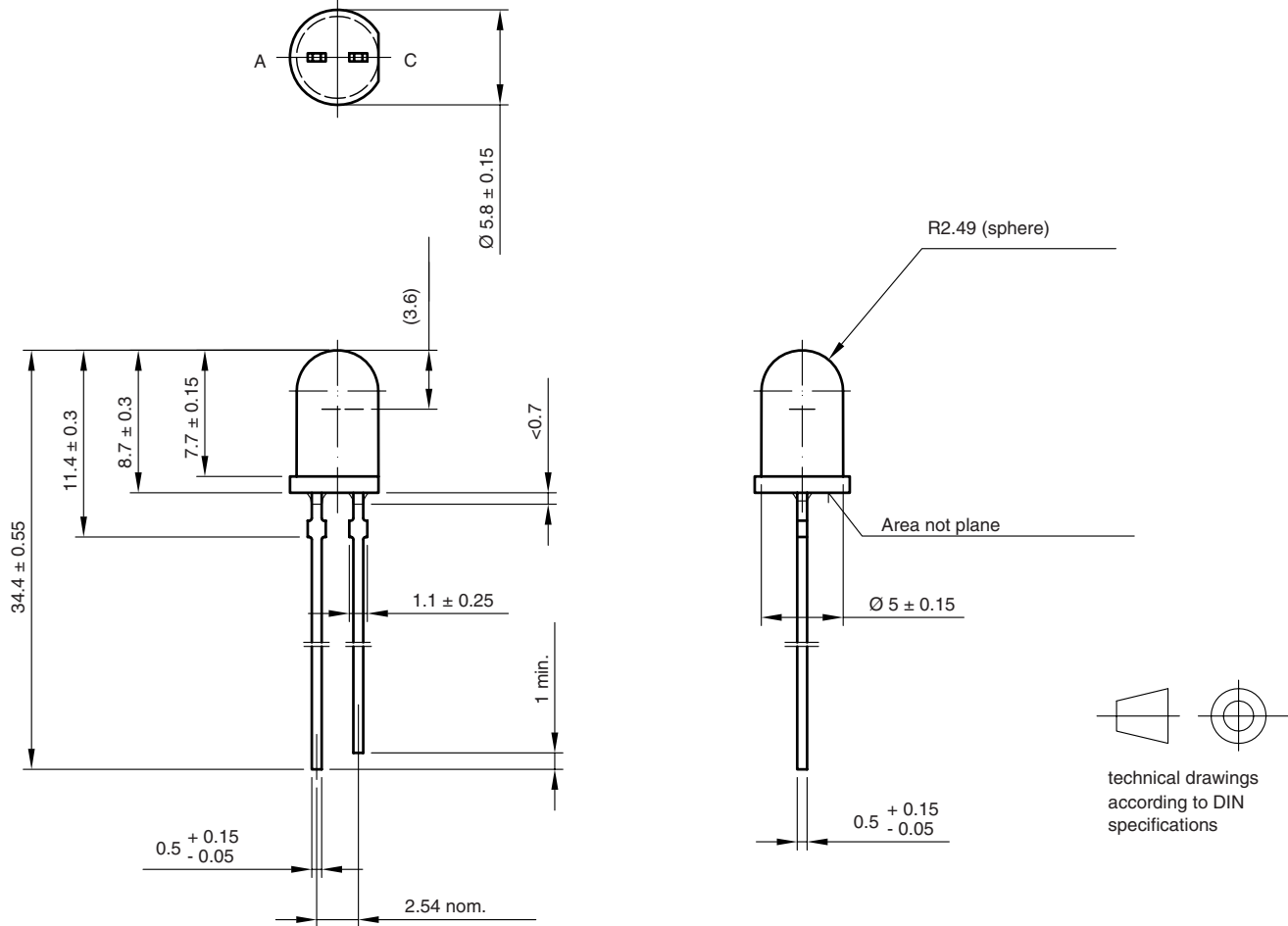


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



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TAPE DIMENSIONS TSAL5300		
OPTION	H ± 0.5 mm	QUANTITY/BOX
CS21Z	22	1000
FSZ	27	1000
GSZ	29	1000
MSZ	25.5	1000

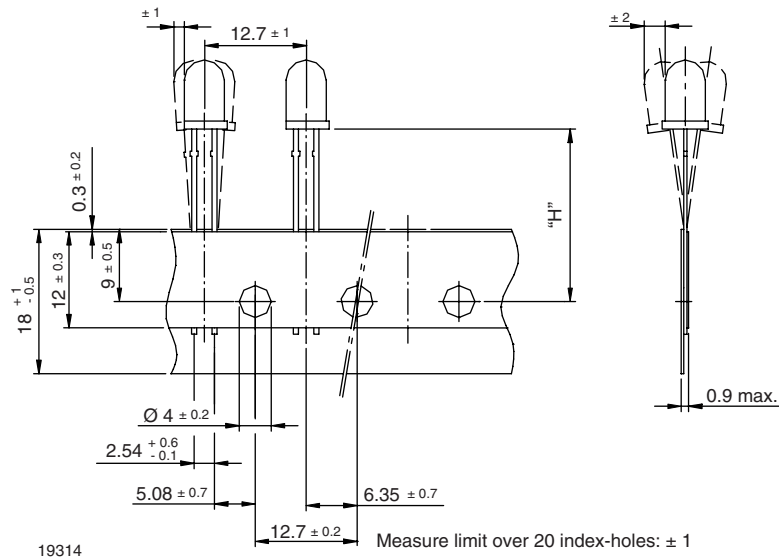


Fig. 10 - Ø 5 mm Devices on Tape

AMMOPACK

The tape is folded in a concertina arrangement and laid in cardboard box.

If components are required with cathode before the anode (figure 12), then start of tape should be taken from the side of the box marked "-". If components are required with anode before cathode, then tape should be taken from the side of the box marked "+".

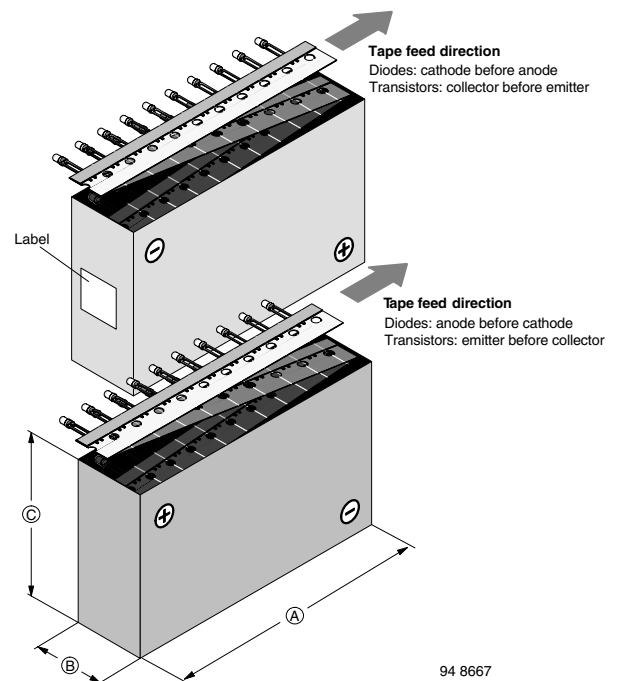


Fig. 11 - Tape Direction



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